

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	("5918119").PN.	USPAT	OR	OFF	2005/03/02 14:52
L2	1	("6586299").PN.	USPAT	OR	OFF	2005/03/02 14:52
L3	1	1 and (MOSFET or salicide or self or aligned or silicide or first or second or third or conductive or dielectric or mask or pattern or capacitor or structure or stacked or hard or revealing or silicon or oxide or nitride or material or oxynitride or high-k or photo or resist)	USPAT	OR	ON	2005/03/02 15:01
L4	1	2 and (MOSFET or salicide or self or aligned or silicide or first or second or third or conductive or dielectric or mask or pattern or capacitor or structure or stacked or hard or revealing or silicon or oxide or nitride or material or oxynitride or high-k or photo or resist)	USPAT	OR	ON	2005/03/02 15:25
L5	1	"6323079".PN.	USPAT; USOCR	OR	ON	2005/03/02 15:06
L6	1	"5792681".PN.	USPAT; USOCR	OR	ON	2005/03/02 15:07
L7	1	"5618749".PN.	USPAT; USOCR	OR	ON	2005/03/02 15:07
L8	1	5 and (MOSFET or salicide or self or aligned or silicide or first or second or third or conductive or dielectric or mask or pattern or capacitor or structure or stacked or hard or revealing or silicon or oxide or nitride or material or oxynitride or high-k or photo or resist)	USPAT	OR	ON	2005/03/02 15:17
L9	1	6 and (MOSFET or salicide or self or aligned or silicide or first or second or third or conductive or dielectric or mask or pattern or capacitor or structure or stacked or hard or revealing or silicon or oxide or nitride or material or oxynitride or high-k or photo or resist)	USPAT	OR	ON	2005/03/02 15:18

L10	1	7 and (MOSFET or salicide or self or aligned or silicide or first or second or third or conductive or dielectric or mask or pattern or capacitor or structure or stacked or hard or revealing or silicon or oxide or nitride or material or oxynitride or high-k or photo or resist)	USPAT	OR	ON	2005/03/02 15:18
L11	0	MOSFET and salicide and (stacked adj structure) and (hard adj mask) and revealing	USPAT	OR	ON	2005/03/02 15:23
L12	2	MOSFET and salicide and (stacked adj structure) and (hard adj mask) and capacitor	USPAT	OR	ON	2005/03/02 15:28
L13	2	12 and (MOSFET or salicide or self or aligned or silicide or first or second or third or conductive or dielectric or mask or pattern or capacitor or structure or stacked or hard or revealing or silicon or oxide or nitride or material or oxynitride or high-k or photo or resist)	USPAT	OR	ON	2005/03/02 15:25
L14	1616	438/197	USPAT	OR	ON	2005/03/02 15:28
L15	1936	438/239	USPAT	OR	ON	2005/03/02 15:28
L16	1849	438/240	USPAT	OR	ON	2005/03/02 15:28
L17	1217	438/680	USPAT	OR	ON	2005/03/02 15:28
L18	187	438/954	USPAT	OR	ON	2005/03/02 15:28
L19	287	438/721	USPAT	OR	ON	2005/03/02 15:29
L20	1609	438/723	USPAT	OR	ON	2005/03/02 15:29
L21	888	438/724	USPAT	OR	ON	2005/03/02 15:29
L22	116	438/755	USPAT	OR	ON	2005/03/02 15:29
L23	689	438/756	USPAT	OR	ON	2005/03/02 15:29
L24	356	438/757	USPAT	OR	ON	2005/03/02 15:29